

CVD METHOD

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Abstract

PURPOSE: To provide a new gas source material in a CVD method for making an insulating film not containing hydrogen.
CONSTITUTION: A film of SiO₂, Si₃N₄, oxynitride, PSG, BSG, BPSG, or other glass, or the like, which does not contain hydrogen, is made by CVD, using Si compound gas, which does not contain a hydrogen bond, oxide gas, which does not have a hydrogen bond, nitride gas, which does not have a hydrogen bond, and/or halogenated gas such as P, B, Ge, As, and/or Sb, etc., which does not have a hydrogen bond.

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